



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#11/K  
between  
6/5/03

In re the Application of: **KANO, Takashi**

Serial No.: **09/532,775**

Group Art Unit: **2828**

Filed: **March 22, 2000**

Examiner: **Tuan M. Nguyen**

P.T.O. Confirmation No.: **8757**

For: **SEMICONDUCTOR LASER DEVICE**

**SUPPLEMENTAL AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450  
Sir:

RECEIVED  
MAY 23 2003  
TECHNOLOGY CENTER 2800  
May 21, 2003

In response to the Office Action dated **April 10, 2003**, extended to **June 10, 2003** by a one-month Petition for Extension of Time, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please amend claim 3 as follows:

C1  
3. (Twice Amended) The semiconductor laser device according to claim 1, wherein  
said first nitride based semiconductor layer further includes said second conductivity type  
cladding layer provided between said active layer and a second conductivity type cladding layer in  
said second nitride based semiconductor layer.